



# RF Power Field Effect Transistors

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed for PCN and PCS base station applications with frequencies from 1930 to 1990 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

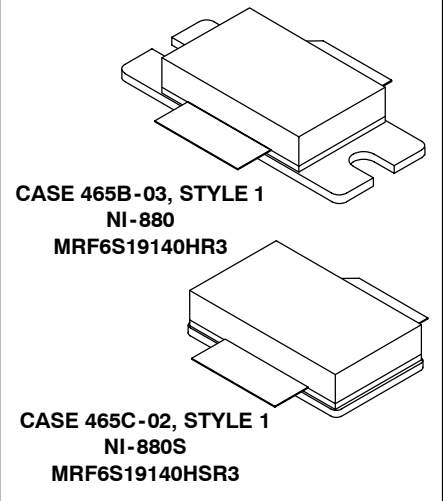
- Typical 2-Carrier N-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 1150$  mA,  $P_{out} = 29$  Watts Avg., Full Frequency Band, IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz, PAR = 9.8 dB @ 0.01% Probability on CCDF.  
 Power Gain — 16 dB  
 Drain Efficiency — 27.5%  
 IM3 @ 2.5 MHz Offset — -37 dBc in 1.2288 MHz Channel Bandwidth  
 ACPR @ 885 kHz Offset — -51 dBc in 30 kHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 1960 MHz, 140 Watts CW Output Power

### Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Optimized for Doherty Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

**MRF6S19140HR3**  
**MRF6S19140HSR3**

**1930-1990 MHz, 29 W AVG., 28 V**  
**2 x N-CDMA**  
**LATERAL N-CHANNEL**  
**RF POWER MOSFETs**



**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +68	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +12	Vdc
Storage Temperature Range	$T_{stg}$	- 65 to +150	°C
Case Operating Temperature	$T_C$	150	°C
Operating Junction Temperature (1,2)	$T_J$	225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 80°C, 140 W CW		0.33	
Case Temperature 77°C, 29 W CW		0.38	

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

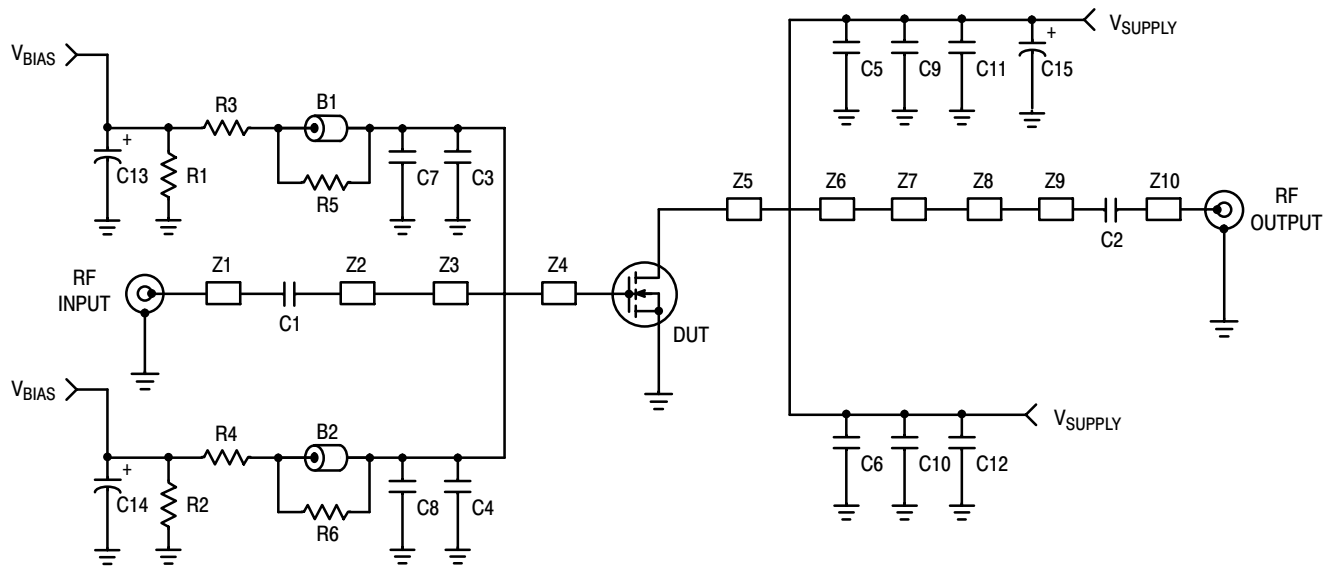
**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Off Characteristics</b>					
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 68\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{Adc}$
<b>On Characteristics</b>					
Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 300\ \mu\text{Adc}$ )	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ( $V_{DD} = 28\text{ Vdc}$ , $I_D = 1150\text{ mAdc}$ , Measured in Functional Test)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 3\text{ Adc}$ )	$V_{DS(on)}$	0.1	0.21	0.3	Vdc
<b>Dynamic Characteristics <sup>(1)</sup></b>					
Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	2	—	pF

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1150\text{ mA}$ ,  $P_{out} = 29\text{ W Avg.}$ ,  $f_1 = 1930\text{ MHz}$ ,  $f_2 = 1932.5\text{ MHz}$  and  $f_1 = 1987.5\text{ MHz}$ ,  $f_2 = 1990\text{ MHz}$ , 2-carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carriers. ACPR measured in 30 kHz Channel Bandwidth @  $\pm 885\text{ kHz}$  Offset. IM3 measured in 1.2288 MHz Channel Bandwidth @  $\pm 2.5\text{ MHz}$  Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	$G_{ps}$	15	16	18	dB
Drain Efficiency	$\eta_D$	26	27.5	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-51	-48	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part is internally matched both on input and output.

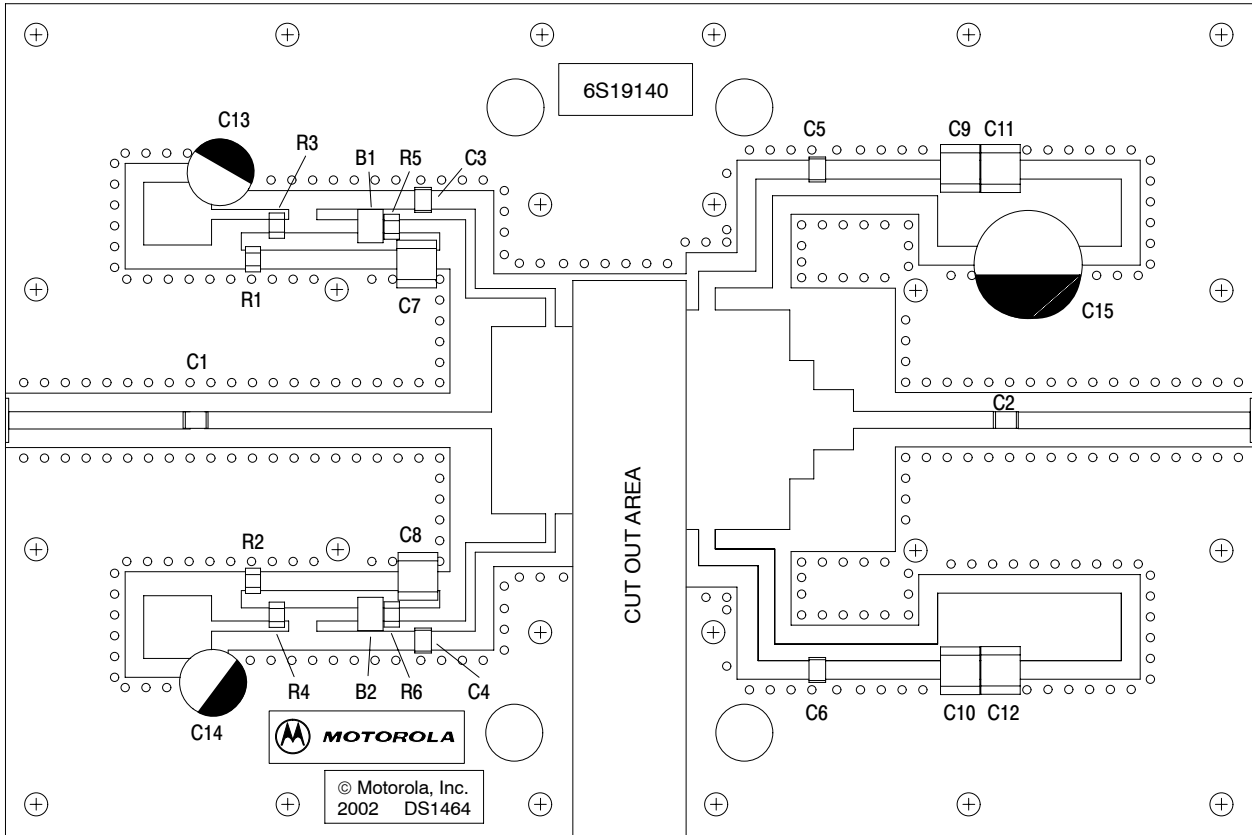


Z1	0.864" x 0.082" Microstrip	Z7	0.115" x 0.569" Microstrip
Z2	1.373" x 0.082" Microstrip	Z8	0.191" x 0.289" Microstrip
Z3	0.282" x 0.900" Microstrip	Z9	0.681" x 0.081" Microstrip
Z4	0.103" x 0.900" Microstrip	Z10	1.140" x 0.081" Microstrip
Z5	0.094" x 1.055" Microstrip	PCB	Arlon GX0300-55-22, 0.030", $\epsilon_r = 2.5$
Z6	0.399" x 1.055" Microstrip		

**Figure 1. MRF6S19140HR3(HSR3) Test Circuit Schematic**

**Table 5. MRF6S19140HR3(HSR3) Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
B1, B2	Beads, Surface Mount	2743019447	Fair-Rite
C1, C2	39 pF Chip Capacitors	ATC100B390JT500XT	ATC
C3, C4, C5, C6	9.1 pF Chip Capacitors	ATC100B9R1CT500XT	ATC
C7, C8, C9, C10, C11, C12	10 $\mu$ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C13, C14	47 $\mu$ F, 50 V Electrolytic Capacitors	EMVY500ADA470MF80G	Nippon
C15	470 $\mu$ F, 63 V Electrolytic Capacitor	ESMG630ELL471MK205	United Chemi-Con
R1, R2	560 k $\Omega$ , 1/4 W Chip Resistors	CRCW12065600FKTA	Vishay
R3, R4	1.0 k $\Omega$ , 1/4 W Chip Resistors	CRCW12061001FKTA	Vishay
R5, R6	12 $\Omega$ , 1/4 W Chip Resistors	CRCW120612R0FKTA	Vishay



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

**Figure 2. MRF6S19140HR3(HSR3) Test Circuit Component Layout**

## TYPICAL CHARACTERISTICS

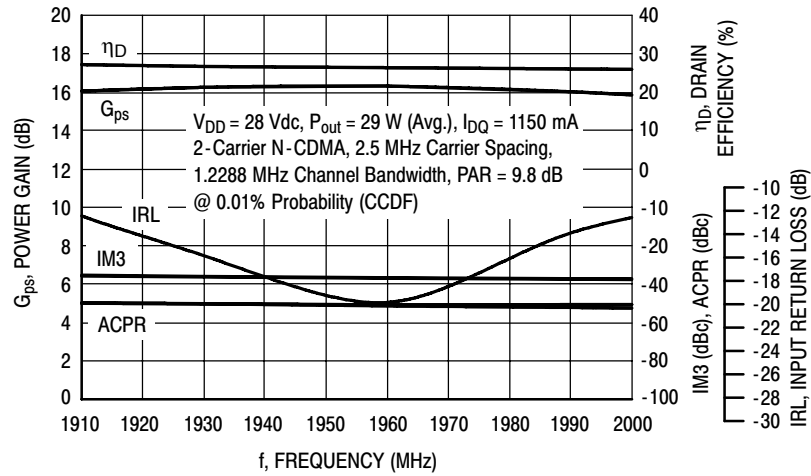


Figure 3. 2-Carrier N-CDMA Broadband Performance @  $P_{out} = 29$  Watts Avg.

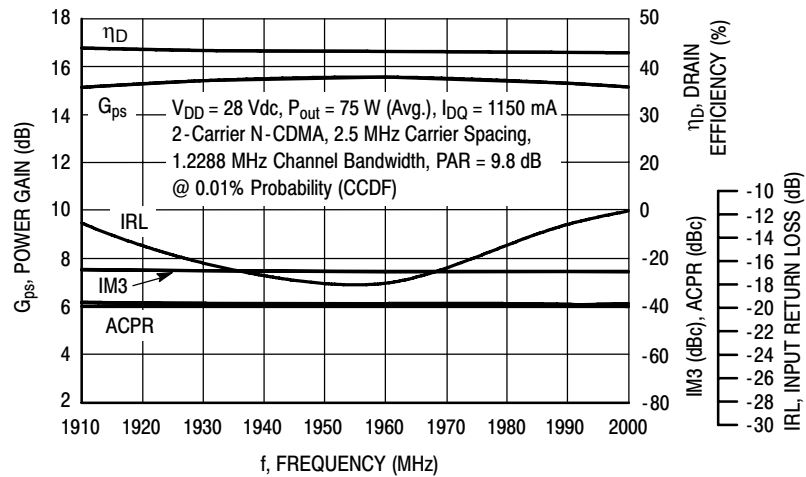


Figure 4. 2-Carrier N-CDMA Broadband Performance @  $P_{out} = 75$  Watts Avg.

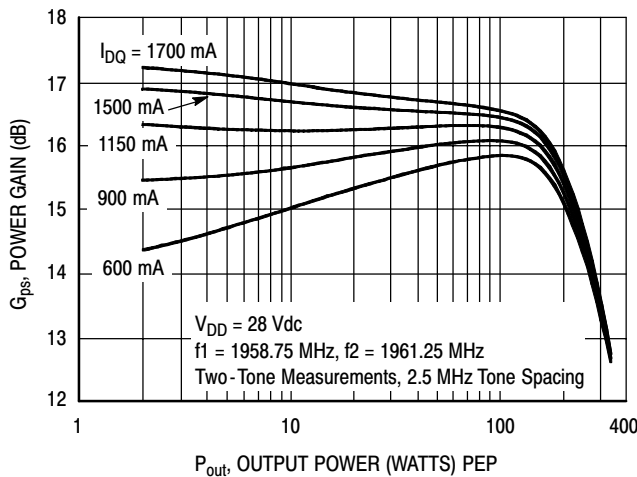


Figure 5. Two-Tone Power Gain versus Output Power

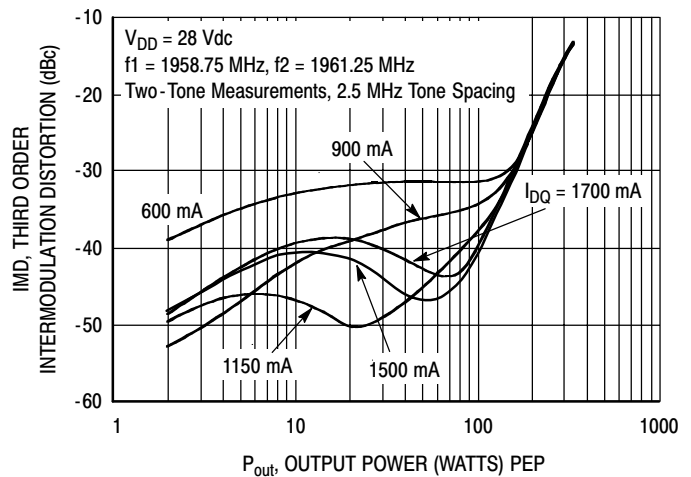
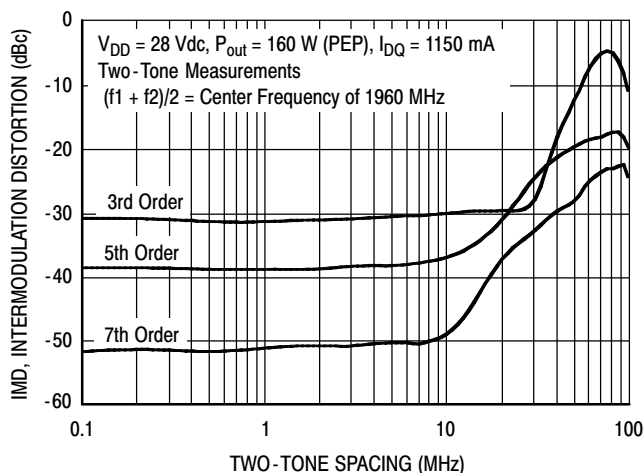
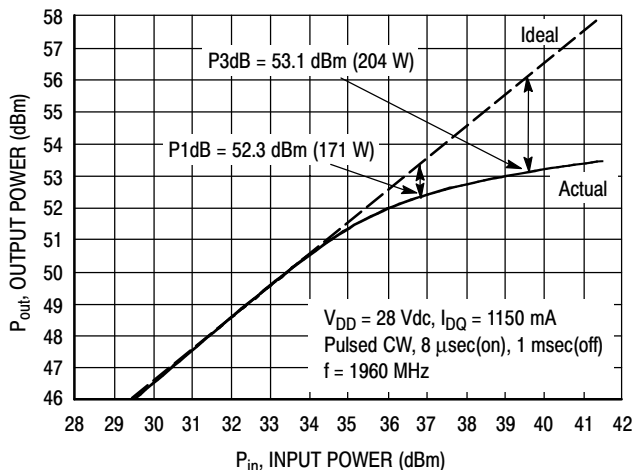


Figure 6. Third Order Intermodulation Distortion versus Output Power

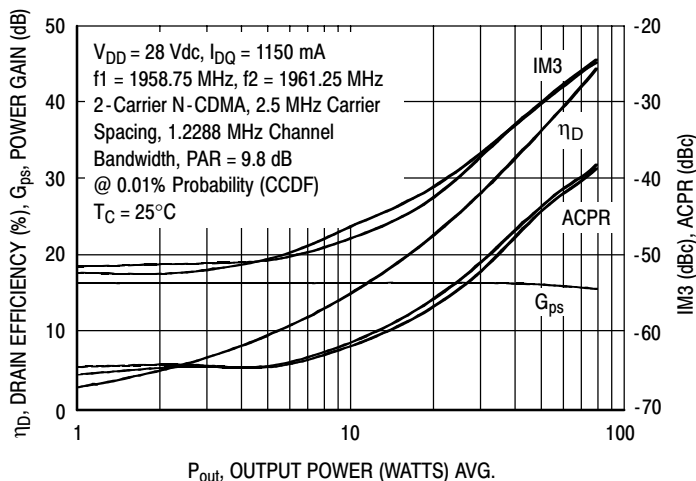
## TYPICAL CHARACTERISTICS



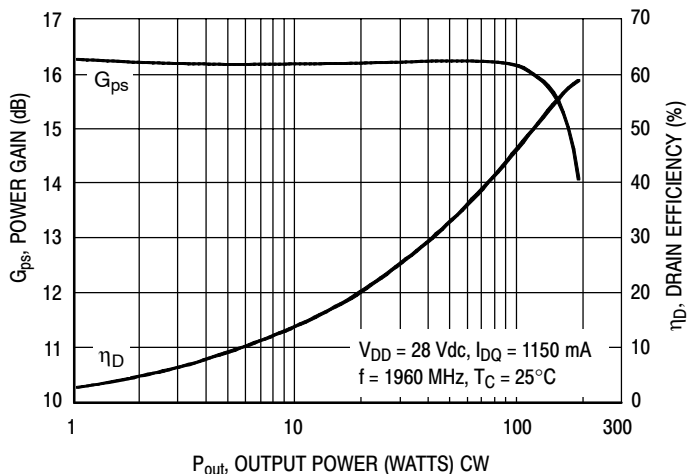
**Figure 7. Intermodulation Distortion Products versus Tone Spacing**



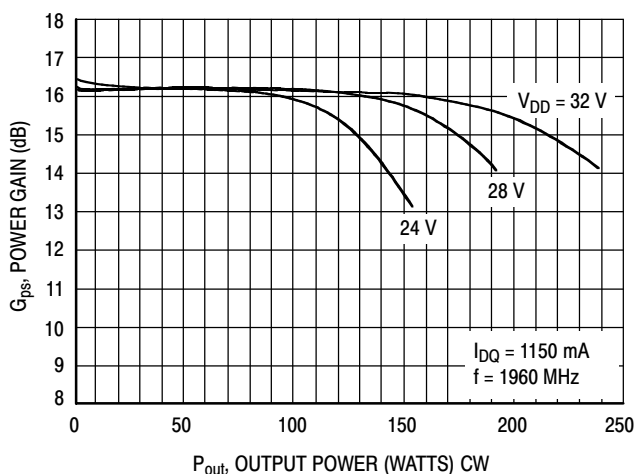
**Figure 8. Pulsed CW Output Power versus Input Power**



**Figure 9. 2-Carrier N-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power**

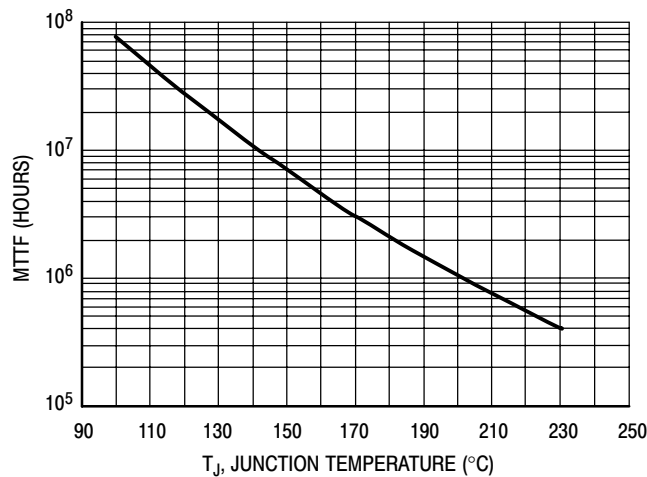


**Figure 10. Power Gain and Drain Efficiency versus CW Output Power**



**Figure 11. Power Gain versus Output Power**

## TYPICAL CHARACTERISTICS

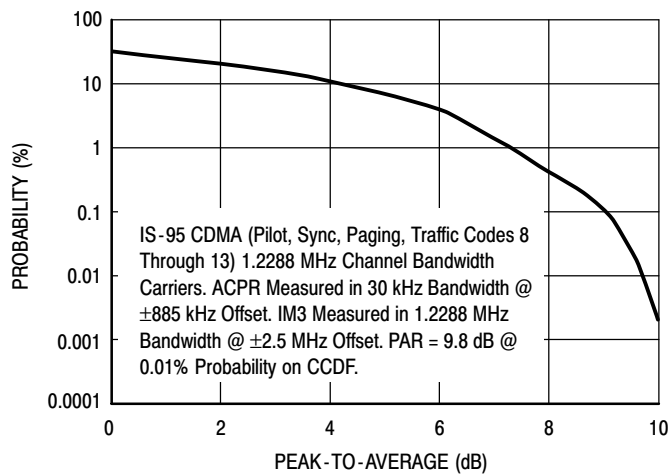


This above graph displays calculated MTTF in hours when the device is operated at  $V_{DD} = 28$  Vdc,  $P_{out} = 29$  W Avg., and  $\eta_D = 27.5\%$ .

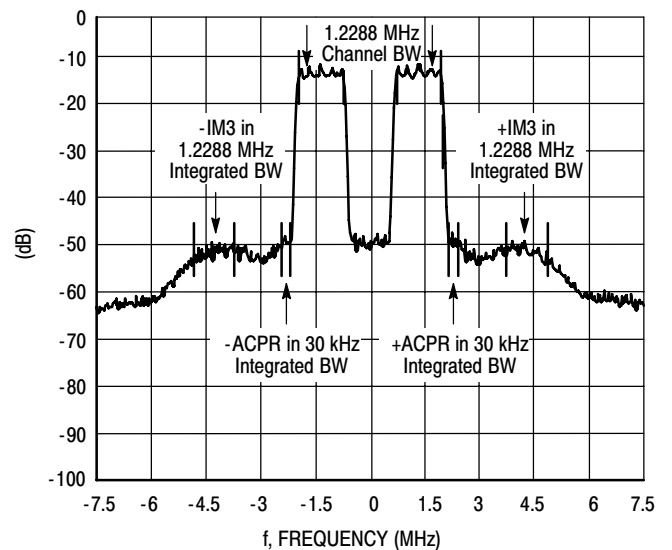
MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.

**Figure 12. MTTF versus Junction Temperature**

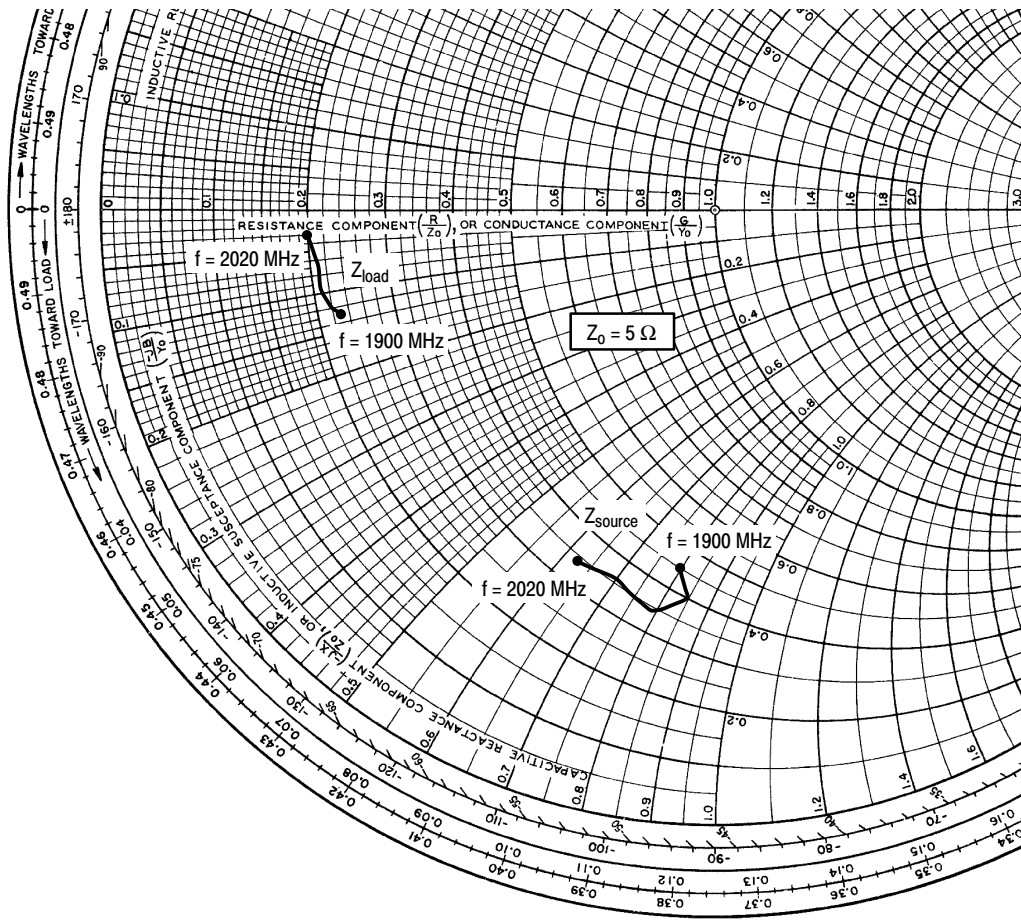
## N-CDMA TEST SIGNAL



**Figure 13. 2-Carrier CCDF N-CDMA**



**Figure 14. 2-Carrier N-CDMA Spectrum**



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 1150 \text{ mA}$ ,  $P_{out} = 29 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
1900	$2.27 - j3.95$	$1.13 - j0.67$
1930	$2.00 - j4.24$	$1.11 - j0.60$
1960	$1.72 - j3.96$	$1.07 - j0.46$
1990	$1.80 - j3.51$	$1.06 - j0.30$
2020	$1.69 - j3.17$	$1.01 - j0.17$

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

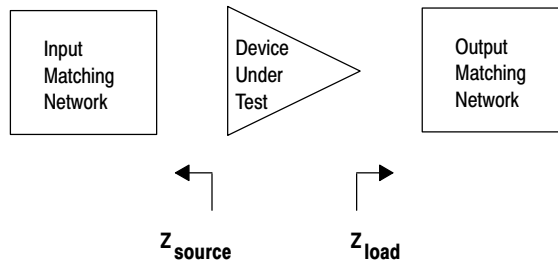
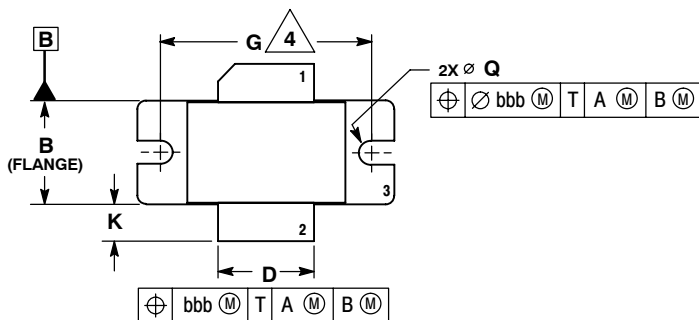


Figure 15. Series Equivalent Source and Load Impedance

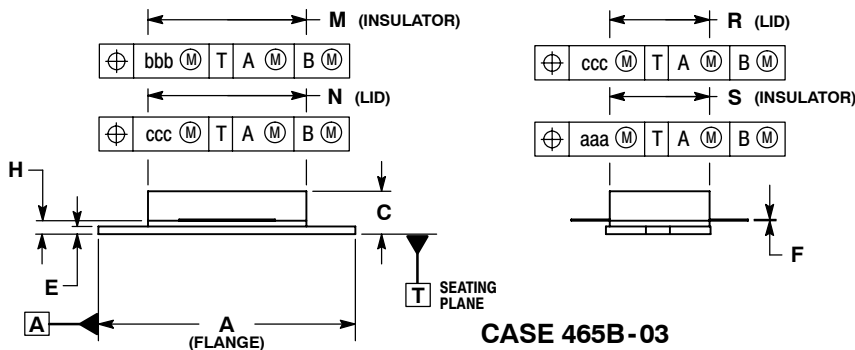


## PACKAGE DIMENSIONS



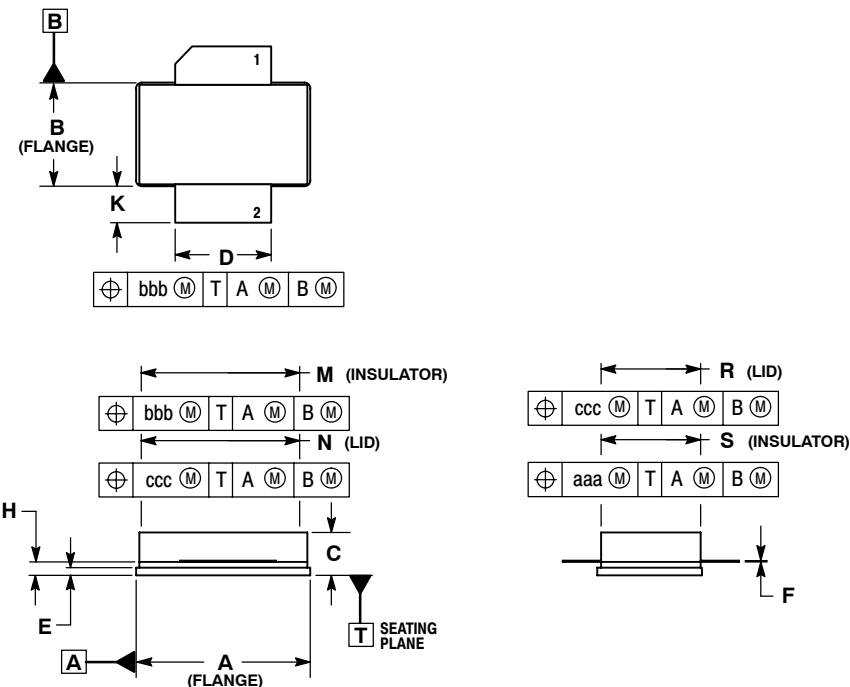
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
  4. RECOMMENDED BOLT CENTER DIMENSION OF .16 (29.57) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.175	0.205	4.44	5.21
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	$\varnothing$ .118	$\varnothing$ .138	$\varnothing$ 3.00	$\varnothing$ 3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	



**CASE 465B-03  
ISSUE D  
NI-880  
MRF6S19140HR3**

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE



**CASE 465C-02  
ISSUE D  
NI-880S  
MRF6S19140HSR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007 REF		0.178 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE

## PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

### Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

### Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

## REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
5	May 2007	<ul style="list-style-type: none"><li>• Removed Lower Thermal Resistance and Low Gold Plating bullets from Features section as functionality is standard, p. 1</li><li>• Removed “Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications” bullet as functionality is standard, p. 1</li><li>• Added “Optimized for Doherty Applications” bullet to Features section, p. 1</li><li>• Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1</li><li>• Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table and related “Continuous use at maximum temperature will affect MTTF” footnote added, p. 1</li><li>• Corrected <math>V_{DS}</math> to <math>V_{DD}</math> in the RF test condition voltage callout for <math>V_{GS(Q)}</math> and added “Measured in Functional Test”, On Characteristics table, p. 2</li><li>• Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2</li><li>• Updated Part Numbers in Table 5, Component Designations and Values, to RoHS compliant part numbers, p. 3</li><li>• Removed lower voltage tests from Fig. 11, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 6</li><li>• Replaced Fig. 12, MTTF versus Junction Temperature with updated graph. Removed <math>\text{Amps}^2</math> and listed operating characteristics and location of MTTF calculator for device, p. 7</li><li>• Added Product Documentation and Revision History, p. 10</li></ul>

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